

SEMiX151GAL12Vs



SEMiX® 1s

SEMiX151GAL12Vs

Features

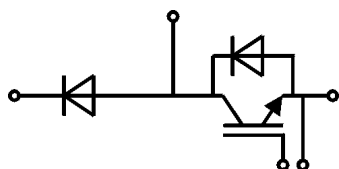
- Homogeneous Si
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- UL recognised file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperature limited to $T_C=125^\circ\text{C}$ max.
- Product reliability results are valid for $T_J=150^\circ\text{C}$



GAL

Absolute Maximum Ratings

Symbol	Conditions	Values	Unit
IGBT			
V_{CES}	$T_J = 25^\circ\text{C}$	1200	V
I_C	$T_J = 175^\circ\text{C}$	$T_C = 25^\circ\text{C}$	231
		$T_C = 80^\circ\text{C}$	176
I_{Cnom}		150	A
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$	450	A
V_{GES}		-20 ... 20	V
t_{psc}	$V_{CC} = 720\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_J = 125^\circ\text{C}$	10
T_J		-40 ... 175	$^\circ\text{C}$
Inverse diode			
I_F	$T_J = 175^\circ\text{C}$	$T_C = 25^\circ\text{C}$	189
		$T_C = 80^\circ\text{C}$	141
I_{Fnom}		150	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$	450	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_J = 25^\circ\text{C}$	900	A
T_J		-40 ... 175	$^\circ\text{C}$
Freewheeling diode			
I_F	$T_J = 175^\circ\text{C}$	$T_C = 25^\circ\text{C}$	189
		$T_C = 80^\circ\text{C}$	141
I_{Fnom}		150	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$	450	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_J = 25^\circ\text{C}$	900	A
T_J		-40 ... 175	$^\circ\text{C}$
Module			
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}$	600	A
T_{stg}		-40 ... 125	$^\circ\text{C}$
V_{isol}	AC sinus 50Hz, $t = 1\text{ min}$	4000	V

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 150\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_J = 25^\circ\text{C}$	1.75	2.20	V
		$T_J = 150^\circ\text{C}$	2.2	2.5	V
V_{CE0}	chipelevel	$T_J = 25^\circ\text{C}$	0.94	1.04	V
		$T_J = 150^\circ\text{C}$	0.88	0.98	V
r_{CE}	$V_{GE} = 15\text{ V}$ chipelevel	$T_J = 25^\circ\text{C}$	5.4	7.7	$\text{m}\Omega$
		$T_J = 150^\circ\text{C}$	8.8	10.1	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C = 6\text{ mA}$	5.5	6	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_J = 25^\circ\text{C}$	0.1	0.3	mA
		$T_J = 150^\circ\text{C}$			mA
C_{ies}	$V_{CE} = 25\text{ V}$	$f = 1\text{ MHz}$	9.0		nF
C_{oes}	$V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	0.89		nF
C_{res}		$f = 1\text{ MHz}$	0.88		nF
Q_G	$V_{GE} = -8\text{ V...} + 15\text{ V}$		1650		nC
R_{Gint}	$T_J = 25^\circ\text{C}$		5.00		Ω

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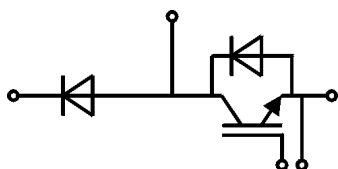
Typical Applications*

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperature limited to $T_C=125^\circ\text{C}$ max.
- Product reliability results are valid for $T_J=150^\circ\text{C}$

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
t _{d(on)}	V _{CC} = 600 V	T _j = 150 °C		319		ns
t _r	I _C = 150 A	T _j = 150 °C		46		ns
E _{on}	V _{GE} = ±15 V	T _j = 150 °C		19.4		mJ
t _{d(off)}	R _{G on} = 1 Ω	T _j = 150 °C		482		ns
t _f	R _{G off} = 1 Ω	T _j = 150 °C		68		ns
E _{off}	di/dt _{on} = 4600 A/μs di/dt _{off} = 1700 A/μs du/dt _{off} = 6700 V/μs	T _j = 150 °C		17.1		mJ
R _{th(j-c)}	per IGBT				0.19	K/W
Inverse diode						
V _F = V _{EC}	I _F = 150 A	T _j = 25 °C		2.1	2.46	V
	V _{GE} = 0 V chiplevel	T _j = 150 °C		2.1	2.4	V
V _{F0}	chiplevel	T _j = 25 °C	1.1	1.3	1.5	V
		T _j = 150 °C	0.7	0.9	1.1	V
r _F	chiplevel	T _j = 25 °C	4.3	5.6	6.4	mΩ
		T _j = 150 °C	7.0	7.8	8.5	mΩ
I _{RRM}	I _F = 150 A	T _j = 150 °C		175		A
Q _{rr}	di/dt _{off} = 4400 A/μs	T _j = 150 °C		27.5		μC
E _{rr}	V _{GE} = -15 V V _{CC} = 600 V	T _j = 150 °C		11.5		mJ
R _{th(j-c)}	per diode				0.31	K/W
Freewheeling diode						
V _F = V _{EC}	I _F = 150 A	T _j = 25 °C		2.1	2.46	V
	V _{GE} = 0 V chiplevel	T _j = 150 °C		2.1	2.4	V
V _{F0}	chiplevel	T _j = 25 °C	1.1	1.3	1.5	V
		T _j = 150 °C	0.7	0.9	1.1	V
r _F	chiplevel	T _j = 25 °C	4.3	5.6	6.4	mΩ
		T _j = 150 °C	7.0	7.8	8.5	mΩ
I _{RRM}	I _F = 150 A	T _j = 150 °C		175		A
Q _{rr}	di/dt _{off} = 4400 A/μs	T _j = 150 °C		27.5		μC
E _{rr}	V _{GE} = -15 V V _{CC} = 600 V	T _j = 150 °C		11.5		mJ
R _{th(j-c)}	per diode				0.31	K/W
Module						
L _{CE}				16		nH
R _{CC'+EE'}	res., terminal-chip	T _C = 25 °C		0.7		mΩ
		T _C = 125 °C		1		mΩ
R _{th(c-s)}	per module			0.075		K/W
M _s	to heat sink (M5)		3		5	Nm
M _t		to terminals (M6)	2.5		5	Nm
						Nm
w				145		g
Temperatur Sensor						
R ₁₀₀	T _C =100°C (R ₂₅ =5 kΩ)			493 ± 5%		Ω
B _{100/125}	R(T)=R ₁₀₀ exp[B _{100/125} (1/T-1/T ₁₀₀)]; T[K];			3550 ±2%		K



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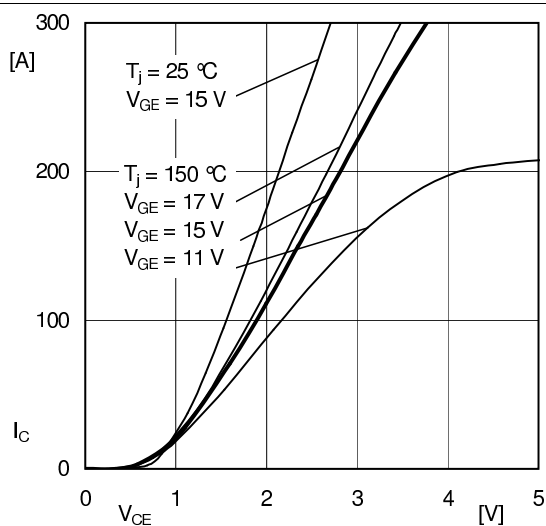


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE'}$

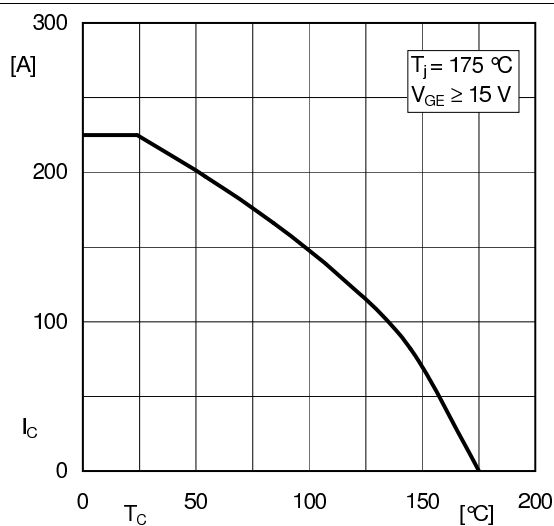


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

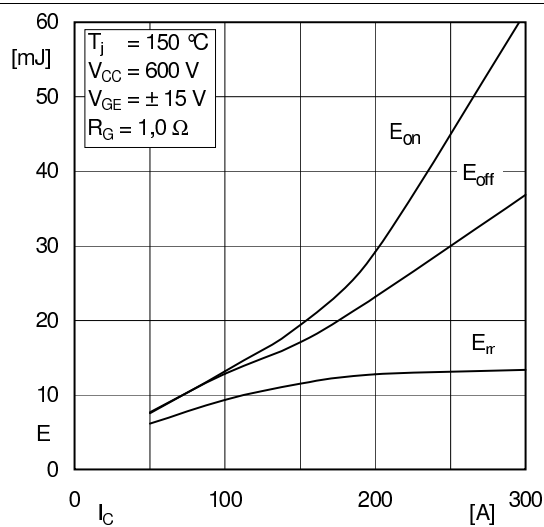


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

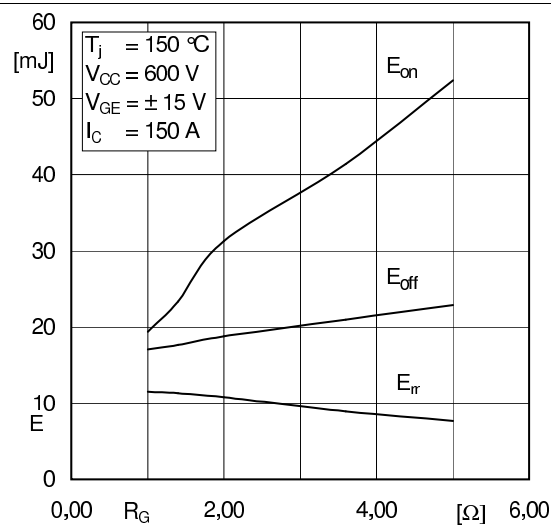


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

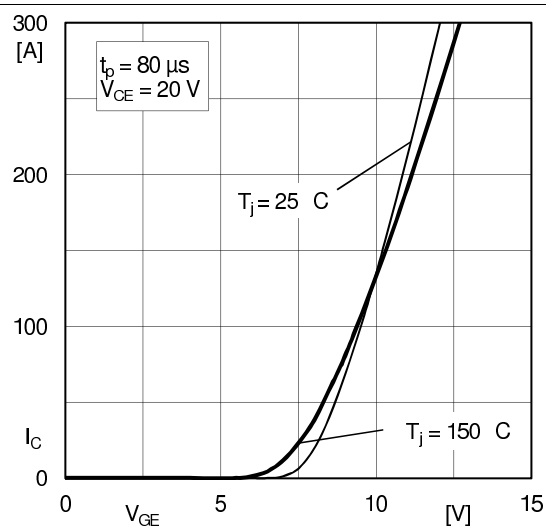


Fig. 5: Typ. transfer characteristic

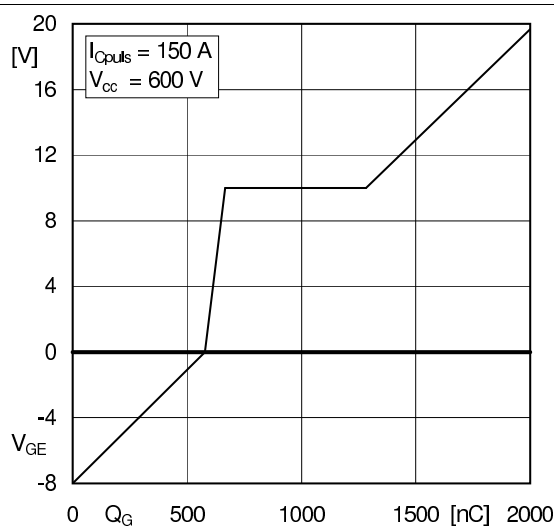


Fig. 6: Typ. gate charge characteristic

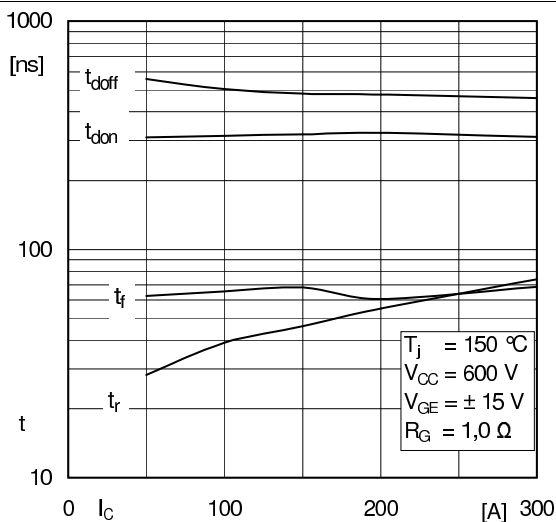


Fig. 7: Typ. switching times vs. I_C

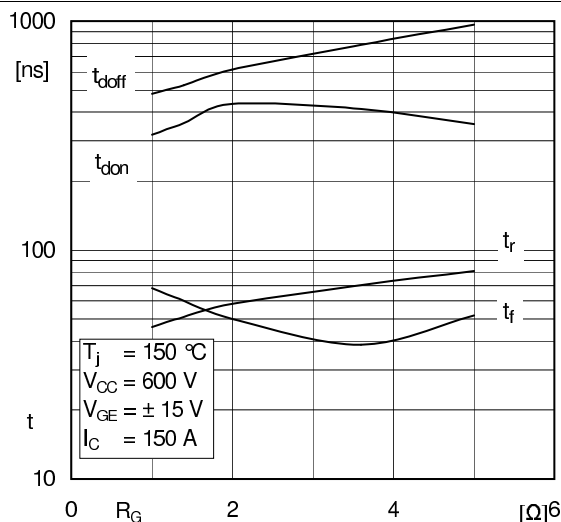


Fig. 8: Typ. switching times vs. gate resistor R_G

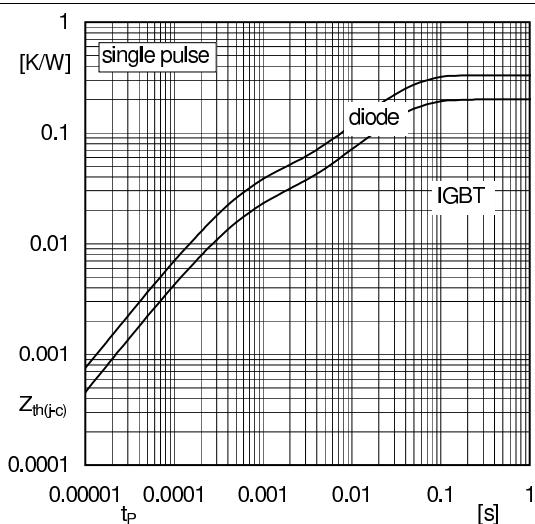


Fig. 9: Typ. transient thermal impedance

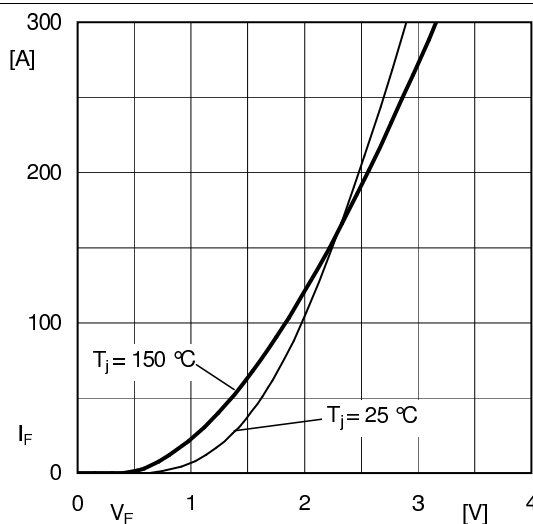


Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC'} + EE'$

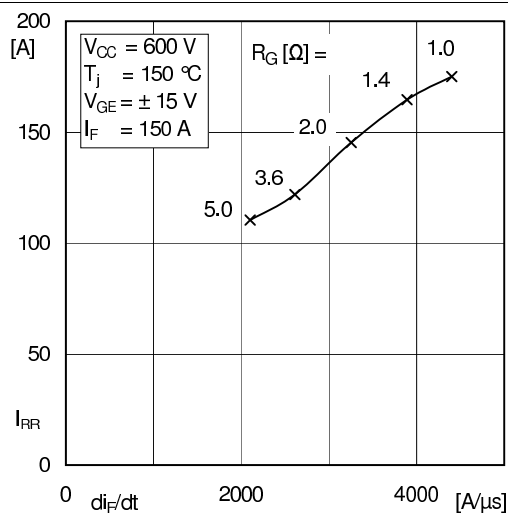


Fig. 11: Typ. CAL diode peak reverse recovery current

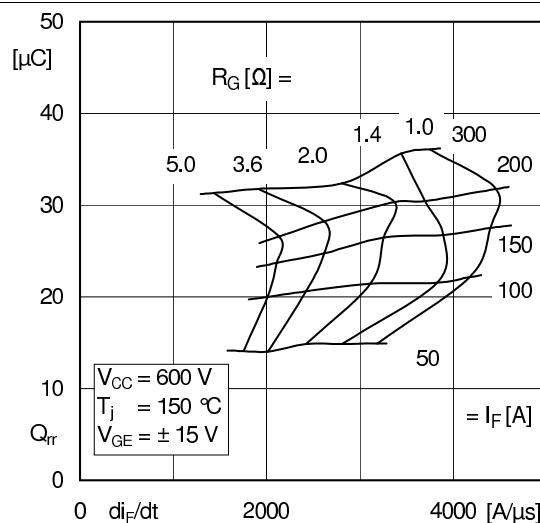
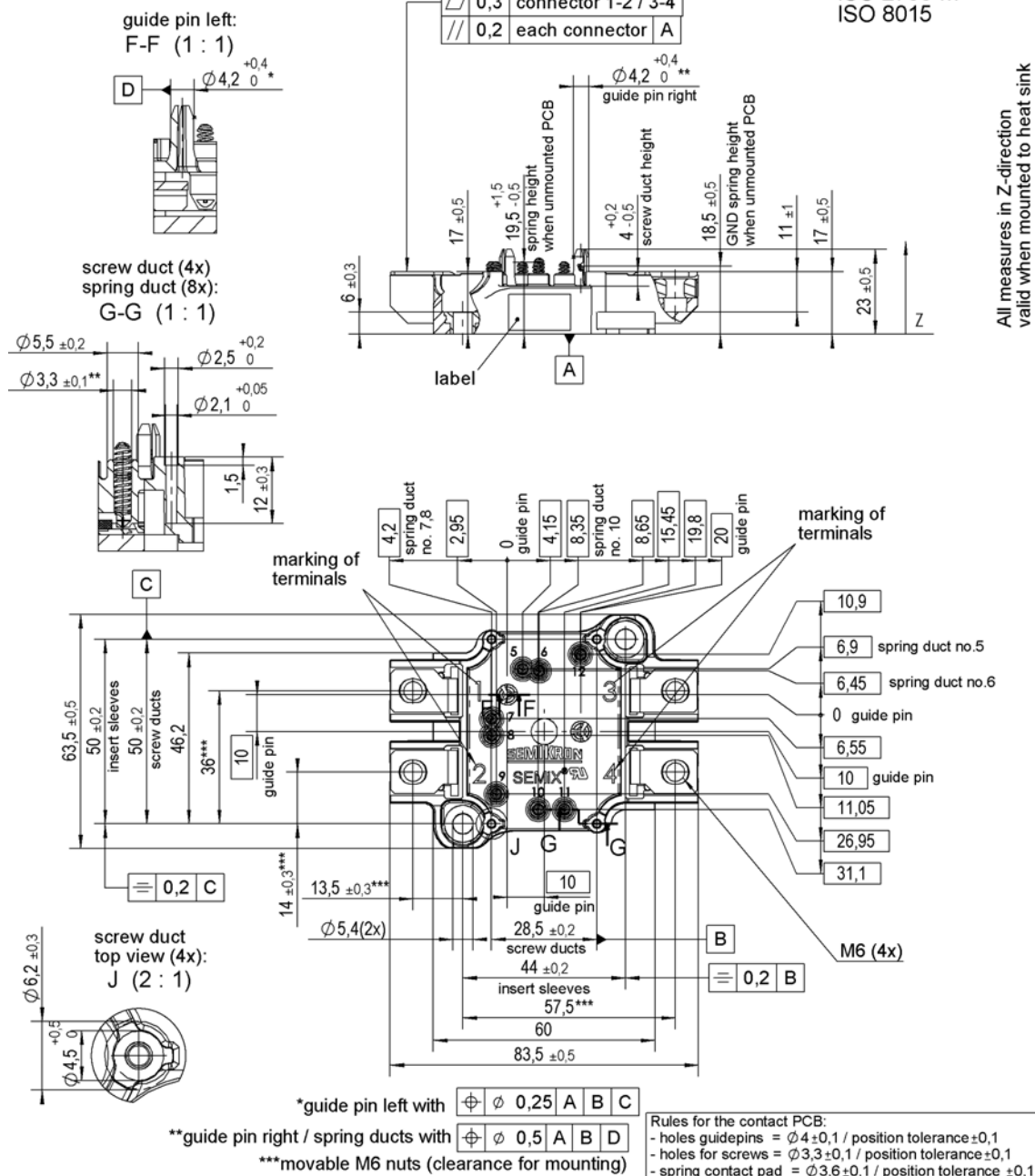


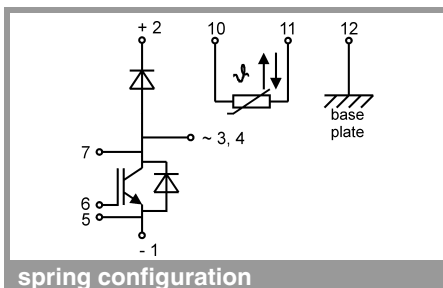
Fig. 12: Typ. CAL diode recovery charge

Case: SEMiX 1s

general tolerance:
ISO 2768-m
ISO 8015



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.